HiPerRF ${ }^{\text {M }}$

## Power MOSFETs

F-Class: MegaHertz Switching

N-Channel Enhancement Mode Avalanche Rated, Low $Q_{g}$, Low
miniBLOC, SOT-227
E1 E153432 Intrinsic $\mathrm{R}_{\mathrm{g}}$, High dV/dt, Low $\mathrm{t}_{\mathrm{rr}}$


| Symbol | Test Conditions | Maximum Ratings |  |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {DS }}$ | $\mathrm{T}_{J}=25^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$ | 1000 | V |
| $\mathrm{V}_{\text {DGR }}$ | $\mathrm{T}_{J}=25^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}, \mathrm{R}_{\mathrm{GS}}=1 \mathrm{M} \Omega$ | 1000 | V |
| $\mathrm{V}_{\text {Gss }}$ | Continuous | $\pm 20$ | V |
| $\mathrm{V}_{\text {GSM }}$ | Transient | $\pm 30$ | V |
| $\mathrm{I}_{\mathrm{D} 25}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | 24 | A |
| $\underline{\mathrm{I} M}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$, Pulse Width Limited by $\mathrm{T}_{\mathrm{JM}}$ | 96 | A |
| $\mathrm{I}_{\text {A }}$ | $\mathrm{T}_{\mathrm{c}}=25^{\circ} \mathrm{C}$ | 24 | A |
| $\mathrm{E}_{\text {AS }}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | 3 | J |
| dV/dt | $\begin{aligned} & \mathrm{I}_{\mathrm{S}} \leq \mathrm{I}_{\mathrm{DM}}, \mathrm{di} / \mathrm{dt} \leq 100 \mathrm{~A} / \mu \mathrm{s}, \mathrm{~V}_{\mathrm{DD}} \leq \mathrm{V}_{\mathrm{DSS}} \\ & \mathrm{~T}_{\mathrm{J}} \leq 150^{\circ} \mathrm{C}, \mathrm{R}_{\mathrm{G}}=2 \Omega \end{aligned}$ | 10 | V/ns |
| $\mathrm{P}_{\mathrm{D}}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | 600 | W |
| $\mathrm{T}_{\mathrm{J}}$ |  | $-55 \ldots+150$ | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {Јм }}$ |  | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ |  | $-55 \ldots+150$ | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | 1.6 mm (0.062 in.) from Case for 10s | 300 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {sold }}$ | Plastic Body for 10s | 260 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{V}_{\text {ISOL }}$ | $50 / 60 \mathrm{~Hz}, \mathrm{RMS} \quad \mathrm{t}=1$ minute | 2500 | V |
|  | $\mathrm{I}_{\text {ISoL }} \leq 1 \mathrm{~mA} \quad \mathrm{t}=1$ second | 3000 | V~ |
| $\mathrm{M}_{\mathrm{d}}$ | Mounting Torque | 1.5/13 | Nm/lb.in. |
|  | Terminal Connection Torque | 1.3/11.5 | Nm/lb.in. |
| Weight |  | 30 | g |

## Features

- RF capable MOSFETs
- Double metal process for low gate resistance
- Avalanche rated
- Low package inductance
- Fast intrinsic rectifier


## Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, $>500 \mathrm{kHz}$ switching
- DC choppers
- Pulse generation
- Laser drivers


## Advantages

- Easy to mount
- Space savings
- High power density

IXFN24N100F

Symbol Test Conditions

| ( $\mathrm{T}_{\mathrm{J}}=2$ | Unless Otherwise Specified) | Min. | Typ. | Max. |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{g}_{\mathrm{ts}}$ | $V_{\text {DS }}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=12 \mathrm{~A}$, Note 1 | 16 | 24 | S |
| $\begin{aligned} & \mathrm{C}_{\text {iss }} \\ & \mathrm{C}_{\text {oss }} \\ & \mathrm{C}_{\mathrm{rss}} \end{aligned}$ | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=25 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |  | $\begin{array}{r} \hline 6600 \\ 760 \\ 230 \end{array}$ | pF pF pF |
| $\begin{aligned} & t_{\mathrm{d}(0 n)} \\ & t_{\mathrm{r}} \\ & t_{\mathrm{d}(\mathrm{flf})} \\ & t_{\mathrm{f}} \\ & \hline \end{aligned}$ | Resistive Switching Times $\begin{aligned} & \mathrm{V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0.5 \cdot \mathrm{~V}_{\mathrm{DSS}}, \mathrm{I}_{\mathrm{D}}=12 \mathrm{~A} \\ & \mathrm{R}_{\mathrm{G}}=1 \Omega \text { (External) } \end{aligned}$ |  | 22 18 52 11 | ns ns ns ns |
| $\begin{aligned} & \mathbf{Q}_{\mathrm{g}(\mathrm{on})} \\ & \mathbf{Q}_{\mathrm{gs}} \\ & \mathbf{Q}_{\mathrm{gd}} \\ & \hline \end{aligned}$ | $\mathrm{V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0.5 \cdot \mathrm{~V}_{\text {DSS }}, \mathrm{I}_{\mathrm{D}}=12 \mathrm{~A}$ |  | $\begin{array}{r} 195 \\ 40 \\ 100 \end{array}$ | nC |
| $\begin{aligned} & \mathbf{R}_{\mathrm{thncc}} \\ & \mathbf{R}_{\mathrm{thncs}} \end{aligned}$ |  |  | 0.05 | $0.21^{\circ} \mathrm{C} / \mathrm{w}$ ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## Source-Drain Diode

| Symbol Test Conditions$\left(\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}\right.$, Unless Otherwise Specified) |  | Characteristic Values |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min. | Typ. | Max |  |
| $\mathrm{I}_{\text {s }}$ | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}$ |  |  | 24 | A |
| $\mathrm{I}_{\text {SM }}$ | Repetitive, Pulse Width Limited by $\mathrm{T}_{\mathrm{JM}}$ |  |  | 96 | A |
| $\mathrm{V}_{\text {sD }}$ | $\mathrm{I}_{\mathrm{F}}=24 \mathrm{~A}, \mathrm{~V}_{\text {GS }}=0 \mathrm{~V}$, Note 1 |  |  | 1.5 | V |
| $\begin{aligned} & t_{\mathrm{rr}} \\ & \mathbf{Q}_{\mathrm{RM}} \\ & \mathrm{I}_{\mathrm{RM}} \end{aligned}$ | $\left\{\begin{array}{l} \mathrm{I}_{\mathrm{F}}=24 \mathrm{~A}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V} \\ -\mathrm{di} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{S} \\ \mathrm{~V}_{\mathrm{R}}=100 \mathrm{~V} \end{array}\right.$ |  | 1.4 10 | 250 | $n s$ $\mu \mathrm{C}$ A |

SOT-227B (IXFN) Outline

(M4 screws (4x) supplied)

| SYM | INCHES |  | MILLIMETERS |  |
| :---: | :---: | :---: | ---: | ---: |
|  | MIN | MAX | MIN | MAX |
| A | 1.240 | 1.255 | 31.50 | 31.88 |
| B | .307 | .323 | 7.80 | 8.20 |
| C | .161 | .169 | 4.09 | 4.29 |
| D | .161 | .169 | 4.09 | 4.29 |
| E | .161 | .169 | 4.09 | 4.29 |
| F | .587 | .595 | 14.91 | 15.11 |
| G | 1.186 | 1.193 | 30.12 | 30.30 |
| H | 1.496 | 1.505 | 38.00 | 38.23 |
| J | .460 | .481 | 11.68 | 12.22 |
| K | .351 | .378 | 8.92 | 9.60 |
| L | .030 | .033 | 0.76 | 0.84 |
| M | .496 | .506 | 12.60 | 12.85 |
| N | .990 | 1.001 | 25.15 | 25.42 |
| O | .078 | .084 | 1.98 | 2.13 |
| P | .195 | .235 | 4.95 | 5.97 |
| Q | 1.045 | 1.059 | 26.54 | 26.90 |
| R | .155 | .174 | 3.94 | 4.42 |
| S | .186 | .191 | 4.72 | 4.85 |
| T | .968 | .987 | 24.59 | 25.07 |
| U | -.002 | .004 | -0.05 | 0.1 |

Note 1: Pulse Test, $\mathrm{t} \leq 300 \mu \mathrm{~s}$; Duty Cycle, $\mathrm{d} \leq 2 \%$.

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| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 25.163.2453.0 | 25.163.4253.0 | 25.190.2053.0 | 25.194.3453.0 | 25.320.4853.1 | 25.320.5253.1 | 25.326.3253.1 | 25.326.3553.1 | 25.330.1 | 1653.1 |
| 25.330.4753.1 | 25.330.5253.1 | 25.334.3253.1 | 25.334.3353.1 | 25.350.2053.0 | 25.352.4753.1 | 25.522.3253.0 | T483C T484C | T485F | T485 |
| T512F-YEB | T513F T514F | T554 T612FSE | 25.161.3453.0 | 25.179.2253.0 | 25.194.3253.0 | 25.325.1253.1 | 25.326.4253.1 | 25.330.0 | 0953.1 |
| 25.332.4353.1 | 25.350.1653.0 | 25.350.2453.0 | 25.352.1453.0 | 25.352.1653.0 | 25.352.2453.0 | 25.352.5453.1 | 25.522.3353.0 | 25.602.4 | 4053.0 |
| 25.640.5053.0 |  |  |  |  |  |  |  |  |  |

